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Bib Data Sheet

CONFIRMATION NO. 6780

SERIAL NUMBER 10/717,149	FILING DATE 11/18/2003 RULE	CLASS 438	GROUP ART UNIT 2818	ATTORNEY DOCKET NO. ATM-262
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APPLICANTS

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** CONTINUING DATA *****

N/A

** FOREIGN APPLICATIONS *****

*N/A***IF REQUIRED, FOREIGN FILING LICENSE GRANTED**

** 02/17/2004

Foreign Priority claimed	<input type="checkbox"/> yes <input checked="" type="checkbox"/> no	STATE OR COUNTRY	SHEETS DRAWING	TOTAL CLAIMS	INDEPENDENT CLAIMS
35 USC 119 (a-d) conditions met	<input checked="" type="checkbox"/> yes <input type="checkbox"/> no	Met after Allowance	CA	3	24
Verified and Acknowledged	<i>[Signature]</i>	Examiner's Signature	Initials		4

ADDRESS

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TITLE *Method of Forming a low voltage gate oxide layer and
 Embedded EEPROM cell and method of forming the same tunnel oxide layer in an
 EEPROM cell.*

FILING FEE	FEES: Authority has been given in Paper No. _____ to charge/credit DEPOSIT ACCOUNT No. _____ for following:	<input type="checkbox"/> All Fees <input type="checkbox"/> 1.16 Fees (Filing) <input type="checkbox"/> 1.17 Fees (Processing Ext. of time) <input type="checkbox"/> 1.18 Fees (Issue)
RECEIVED 1054		

In the Title:

Please replace the title with:

METHOD OF FORMING A LOW VOLTAGE GATE OXIDE LAYER AND TUNNEL
OXIDE LAYER IN AN EEPROM CELL